

# MMBF170LT1

## Power MOSFET 500 mA, 60 V N-Channel SOT-23

### Features

- Pb-Free Packages are Available

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	Vdc
Drain-Gate Voltage	$V_{DGS}$	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive ( $t_p \leq 50 \mu s$ )	$V_{GS}$ $V_{GSM}$	$\pm 20$ $\pm 40$	Vdc Vpk
Drain Current - Continuous - Pulsed	$I_D$ $I_{DM}$	0.5 0.8	Adc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1.) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	225 1.8	mW mW/ $^\circ C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ C$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

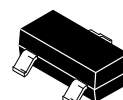
1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.



ON Semiconductor®

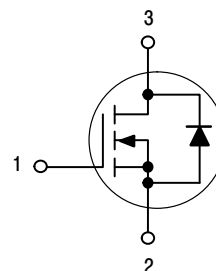
<http://onsemi.com>

500 mA, 60 V  
 $R_{DS(on)} = 5 \Omega$

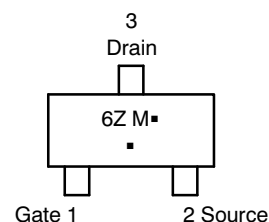


SOT-23  
CASE 318  
STYLE 21

### N-Channel



### MARKING DIAGRAM & PIN ASSIGNMENT



6Z = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# MMBF170LT1

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Drain-Source Breakdown Voltage (V <sub>GS</sub> = 0, I <sub>D</sub> = 100 μA)	V <sub>(BR)DSS</sub>	60	-	Vdc
Gate-Body Leakage Current, Forward (V <sub>GSF</sub> = 15 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	-	10	nAdc

### ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0 mA)	V <sub>GS(th)</sub>	0.8	3.0	Vdc
Static Drain-Source On-Resistance (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 200 mA)	r <sub>DS(on)</sub>	-	5.0	Ω
On-State Drain Current (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0)	I <sub>D(off)</sub>	-	0.5	μA

### DYNAMIC CHARACTERISTICS

Input Capacitance (V <sub>DS</sub> = 10 Vdc, V <sub>GS</sub> = 0 V, f = 1.0 MHz)	C <sub>iss</sub>	-	60	pF
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### SWITCHING CHARACTERISTICS (Note 1)

Turn-On Delay Time	(V <sub>DD</sub> = 25 Vdc, I <sub>D</sub> = 500 mA, R <sub>gen</sub> = 50 Ω) Figure 1	t <sub>d(on)</sub>	-	10	ns
Turn-Off Delay Time		t <sub>d(off)</sub>	-	10	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBF170LT1	SOT-23 (TO-236)	3,000 Tape & Reel
MMBF170LT1G	SOT-23 (TO-236) (Pb-Free)	3,000 Tape & Reel
MMBF170LT3	SOT-23 (TO-236)	10,000 Tape & Reel
MMBF170LT3G	SOT-23 (TO-236) (Pb-Free)	10,000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

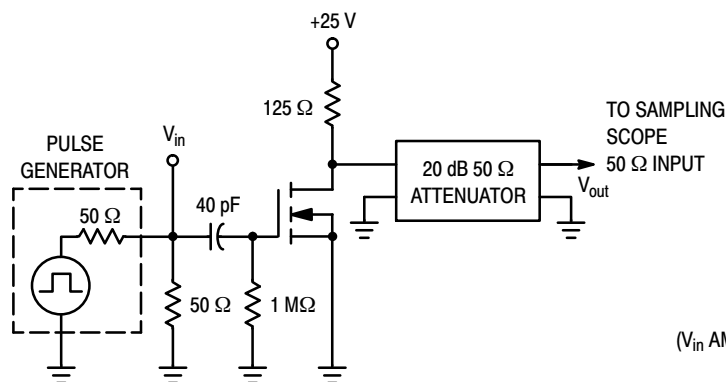


Figure 1. Switching Test Circuit

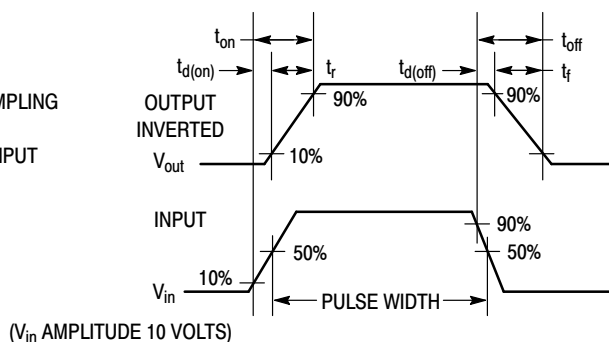


Figure 2. Switching Waveform

TYPICAL ELECTRICAL CHARACTERISTICS

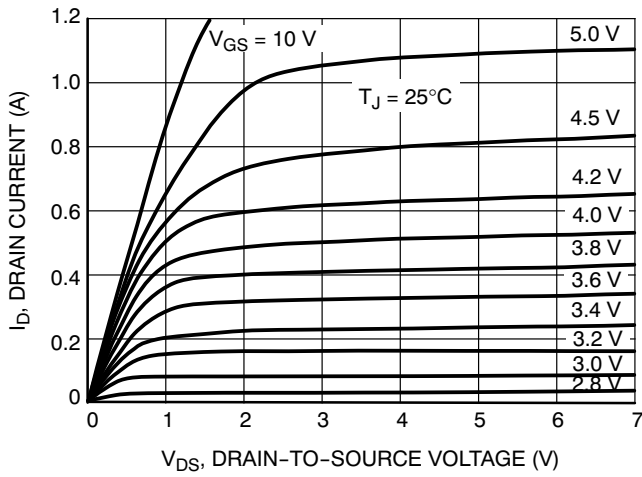


Figure 3. On-Region Characteristics

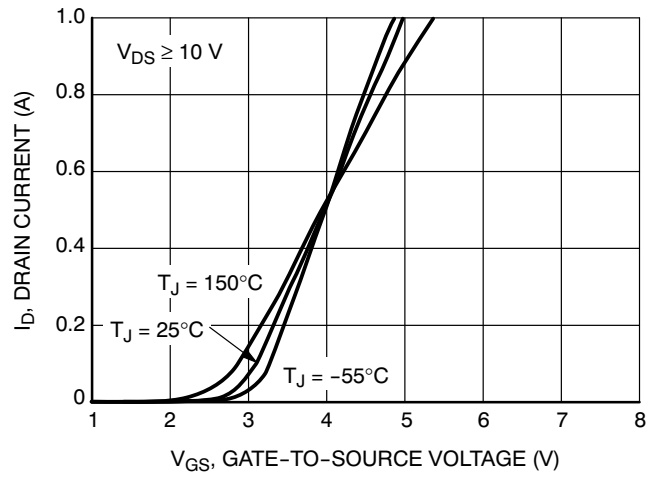


Figure 4. Transfer Characteristics

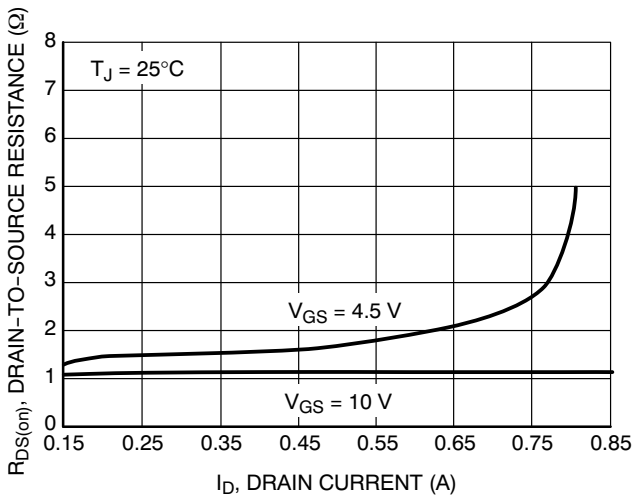


Figure 5. On-Resistance vs. Drain Current and Gate Voltage

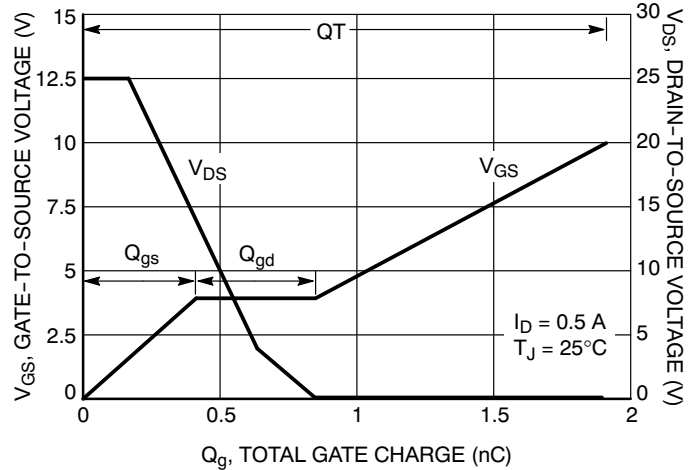


Figure 6. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

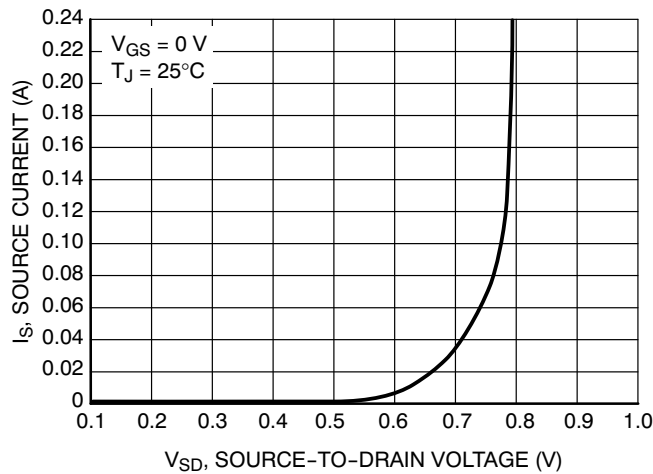


Figure 7. Diode Forward Voltage vs. Current

TYPICAL ELECTRICAL CHARACTERISTICS

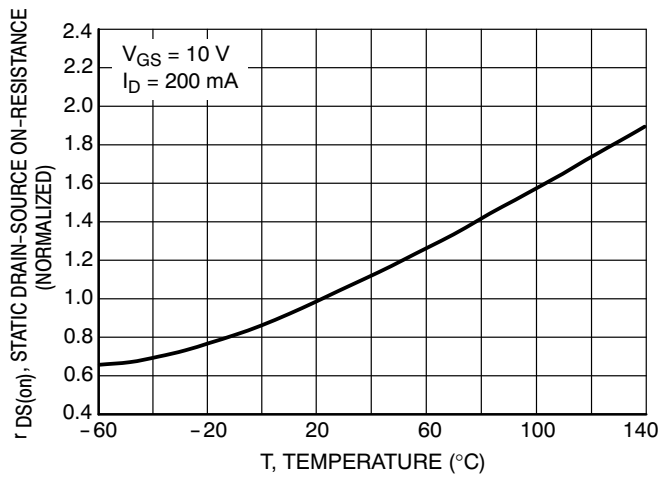


Figure 8. Temperature versus Static Drain-Source On-Resistance

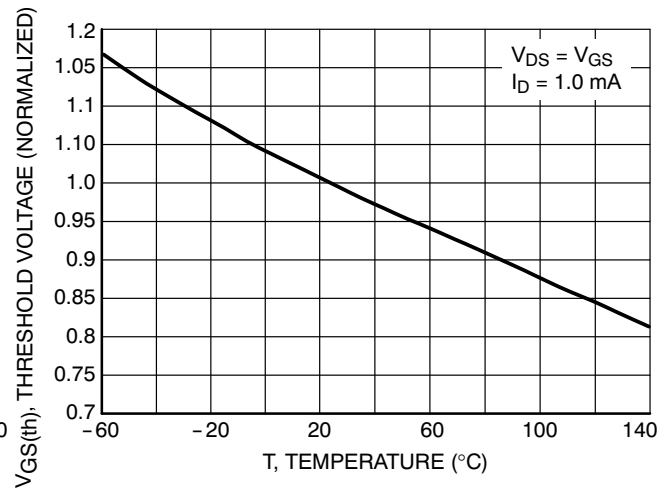


Figure 9. Temperature versus Gate Threshold Voltage

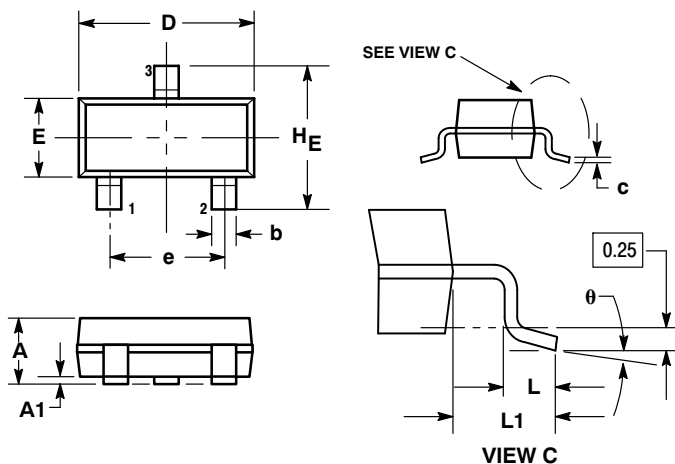
# MMBF170LT1

## PACKAGE DIMENSIONS

### SOT-23 (TO-236)

CASE 318-08

ISSUE AN



#### NOTES:

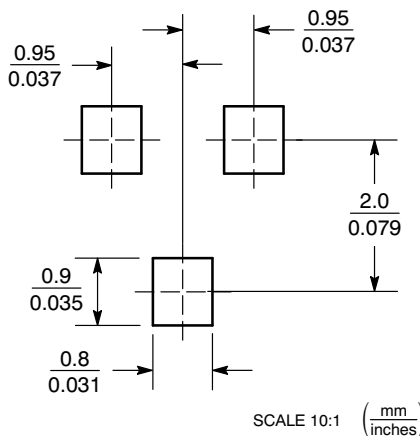
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

#### STYLE 21:


1. GATE
2. SOURCE
3. DRAIN

### SOLDERING FOOTPRINT\*



### SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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